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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete If Known

Application Number: 09/523,990
Filing Date: March 13, 2000
First Named Inventor: **MOU-SHIUNG LIN**
Art Unit:2887
Examiner Name: **DANIEL I. WALSH**

Sheet **1** of **3**

Attorney Docket No: 085027-0026

US PATENT DOCUMENTS

Examiner Initial *	Cite No	Document Number	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or RelevantFigures Appear
		NONE			

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines, Where Relevant Passages or RelevantFigures Appear	T[2]
		NONE				

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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	2	EDELSTEIN, D.C., "Advantages of Copper Interconnects," Proceedings of the 12th International IEEE VLSI Multilevel Interconnection Conference (1995) pgs. 301-307	
	3	THENG, C. et al. "An Automated Tool Deployment for ESD (Electro-Static-Discharge) Correct-by-Construction Strategy in 90 nm Process," IEEE International Conference on Semiconductor Electronics (2004) pgs. 61-67	
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	8	LEE, Y-H. et al. "Effect of ESD Layout on the Assembly Yield and Reliability," International Electron Devices Meeting (2006) pgs. 1-4	

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[1] EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. [2] Applicant's unique citation designation number (optional). [3] Applicant is to place a check mark here if English language Translation is attached

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	9	YEOH, T-S. "ESD Effects On Power Supply Clamps," Proceedings of the 6th International Sympoisum on Physical & Failure Analysis of Integrated Circuits (1997) pgs. 121-124	
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	21	GEFFKEN, R. M. "An Overview of Polyimide Use in Integrated Circuits and Packaging," Proceedings of the Third International Symposium on Ultra Large Scale Integration Science and Technology (1991) pgs. 667-677	
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